

INA19xA-Q1 共模电压范围为 -16V 至 80V 的分流监测计

1 特性

- 适用于汽车电子 应用
- 宽共模电压范围：
-16V 至 80V
- 低误差：3% 过热（最大值）
- 带宽：高达 500kHz
- 三种传递函数：20V/V、50V/V 和 100V/V
- 完整的电流感测解决方案

2 应用

- 焊接设备
- 车身控制模块
- 负载健康状况监视
- 电信设备
- 混合动力汽车 (HEV)/电动汽车 (EV) 动力传动
- 电源管理
- 电池充电器

3 说明

INA19xA-Q1 系列是电压输出分流监测计，能够在 -16V 至 80V 范围内的共模电压下感测分流器两端的压降，与 INA19xA 电源电压无关。该系列器件提供三种输出电压级别：20V/V、50V/V 和 100V/V。500kHz 带宽方便用于电流控制回路和直流电机健康状态监控。INA193A–INA195A 器件与 INA196A–INA198A 器件的功能相同，但引脚配置有所不同。

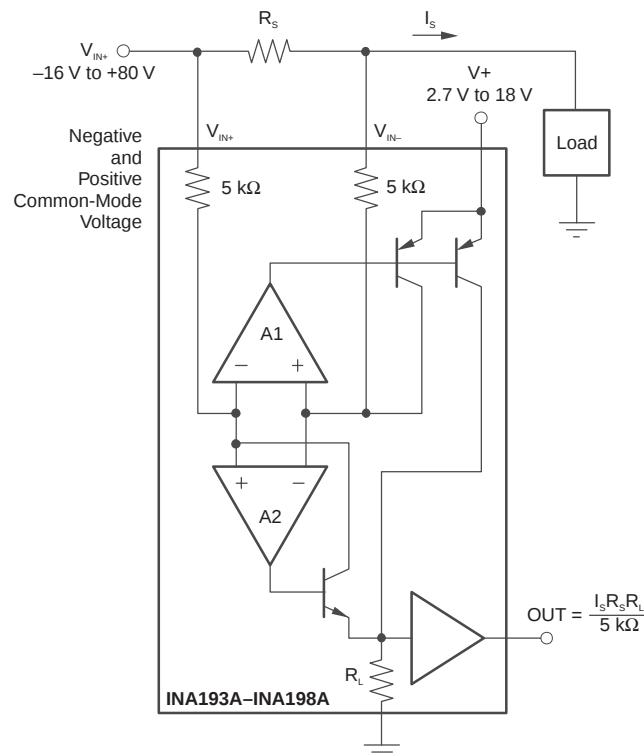
INA19xA-Q1 由 2.7V 至 18V 单电源供电运行。这些器件均在 -40°C 至 125°C 的扩展运行温度范围内额定运行，并且采用节省空间的 SOT-23 封装。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
INA19xA-Q1	SOT-23 (5)	2.90mm x 1.60mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



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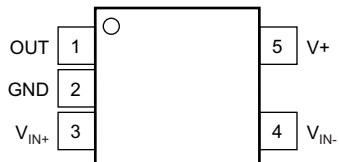
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

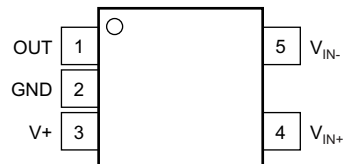
Changes from Revision C (October 2008) to Revision D	Page
• 已添加 ESD 额定值表，特性 描述 部分，器件功能模式，应用和实施部分，电源相关建议部分，布局部分，器件和文档支持部分以及机械、封装和可订购信息部分	1
• Added Input Bias Current vs Common Mode Voltage Vs=5 V graph to <i>Typical Characteristics</i>	7
• Added Input Bias Current vs Common Mode Voltage Vs=12 V graph to <i>Typical Characteristics</i>	7

5 Pin Configuration and Functions

**DBV Package
5-Pin SOT-23
INA193A-Q1, INA194A-Q1, INA195A-Q1 Top View**



**DBV Package
5-Pin SOT-23
INA196A-Q1, INA197A-Q1, INA198A-Q1 Top View**



Pin Functions

NAME	PIN		TYPE	DESCRIPTION
	INA193A-Q1, INA194A-Q1, INA195A-Q1	INA196A-Q1, INA197A-Q1, INA198A-Q1		
GND	2	2	GND	Ground
OUT	1	1	O	Output voltage
V+	5	3	Analog	Power supply, 2.7 to 18 V
V _{IN+}	3	4	I	Connect to supply side of shunt resistor
V _{IN-}	4	5	I	Connect to load side of shunt resistor

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
Supply voltage		18	V
Differential input voltage range, analog inputs ($V_{IN+} - V_{IN-}$)	-18	18	V
Common-mode voltage range ⁽²⁾	-16	80	V
Analog output voltage range ⁽²⁾	OUT	GND – 0.3 (V+) + 0.3	V
Input current into any pin ⁽²⁾		5	mA
Junction temperature		150	°C
Storage temperature, T_{stg}	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input voltage at any pin may exceed the voltage shown if the current at that pin is limited to 5 mA.

6.2 ESD Ratings

	VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±4000
	Charged-device model (CDM), per AEC Q100-011	±1000
	Machine model	±200

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
V_{CM} Common-mode input voltage		12		V
$V+$ Operating supply voltage		12		V
T_A Operating free-air temperature	-40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		INA19xA-Q1	UNIT
		DBV (SOT-23)	
		5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	221.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	144.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	49.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	26.1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	49	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics

 $V_S = 12\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{SENSE} = 100\text{ mV}$ (unless otherwise noted) Full range $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
INPUT							
V _{SENSE}	Full-scale input voltage	V _{SENSE} = V _{IN+} - V _{IN-}	25°C	0.15 (V _S - 0.2)/Gain			V
V _{CM}	Common-mode input		Full range	-16		80	V
CMR	Common-mode rejection	V _{IN+} = -16 V to 80 V	25°C	80	94		dB
		V _{IN+} = 12 V to 80 V	Full range	100	120		
V _{OS}	Offset voltage, RTI		25°C	±0.5		2	mV
			Full range	0.5		3	
dV _{OS} /dT	Offset voltage vs temperature		Full range	2.5			μV/°C
PSR	Offset voltage vs power supply	V _S = 2.7 V to 18 V, V _{IN+} = 18 V	Full range	5		100	μV/V
I _B	Input bias current	V _{IN-} pin	Full range	±8		±23	μA
OUTPUT (V _{SENSE} ≥ 20 mV)							
G	Gain	INA193A, INA196A	25°C	20		V/V	
		INA194A, INA197A		50			
		INA195A, INA198A		100			
	Gain error	V _{SENSE} = 20 mV to 100 mV	25°C	±0.2%	±1%		
			Full range	±2%			
	Total output error ⁽¹⁾		25°C	±0.75%	±2.2%		
			Full range	±1%	±3%		
	Nonlinearity error	V _{SENSE} = 20 mV to 100 mV	25°C	±0.002%	±0.1%		
R _O	Output impedance		25°C	1.5		Ω	
	Maximum capacitive load	No sustained oscillation	25°C	10		nF	
OUTPUT (V _{SENSE} < 20 mV) ⁽²⁾							
V _{OUT}	Output voltage	All devices	25°C	300		mV	
				300			
		INA193A, INA196A		0.4		V	
		INA194A, INA197A		1			
		INA195A, INA198A		2			
VOLTAGE OUTPUT ⁽³⁾							
	Swing to V+ power-supply rail	R _L = 100 kΩ to GND	Full range	V+ - 0.1	V+ - 0.2	V	
	Swing to GND ⁽⁴⁾	R _L = 100 kΩ to GND	Full range	V _{GND} + 3	V _{GND} + 50	mV	

(1) Total output error includes effects of gain error and V_{OS} .

(2) For details on this region of operation, see [Accuracy Variations as a Result Of \$V_{SENSE}\$ and Common Mode Voltage](#).

(3) See [Figure 7](#).

(4) Specified by design

Electrical Characteristics (continued)

$V_S = 12\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{SENSE} = 100\text{ mV}$ (unless otherwise noted) Full range $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		T _A	MIN	TYP	MAX	UNIT
FREQUENCY RESPONSE								
BW	Bandwidth	INA193A, INA196A	C _{LOAD} = 5 pF	25°C	500		kHz	
		INA194A, INA197A			300			
		INA195A, INA198A			200			
Phase margin		C _{LOAD} < 10 nF		25°C	40		°	
SR	Slew rate				1		V/μs	
t _s	Settling time (1%)	V _{SENSE} = 10 mV to 100 mV _{PP} , C _{LOAD} = 5 pF		25°C	2		μs	
NOISE, RTI								
Voltage noise density				25°C	40		nV/√Hz	
POWER SUPPLY								
V _S	Operating voltage			Full range	2.7	18	V	
I _Q	Quiescent current	V _{OUT} = 2 V		Full range	700	1250	μA	
		INA193A, INA194A, INA196A, INA197A	V _{SENSE} = 0 mV	Full range	370	950		
		INA195A, INA198A			370	1050		
TEMPERATURE RANGE								
Operating temperature					−40	125	°C	
Storage temperature					−65	150	°C	

6.6 Typical Characteristics

$T_A = 25^\circ\text{C}$, $V_S = 12\text{ V}$, $V_{IN+} = 12\text{ V}$, and $V_{SENSE} = 100\text{ mV}$ (unless otherwise noted)

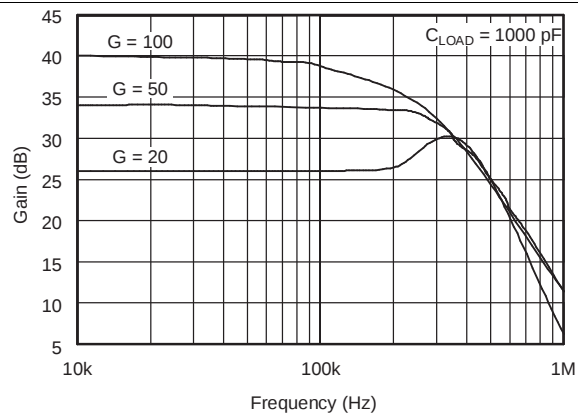


Figure 1. Gain vs Frequency

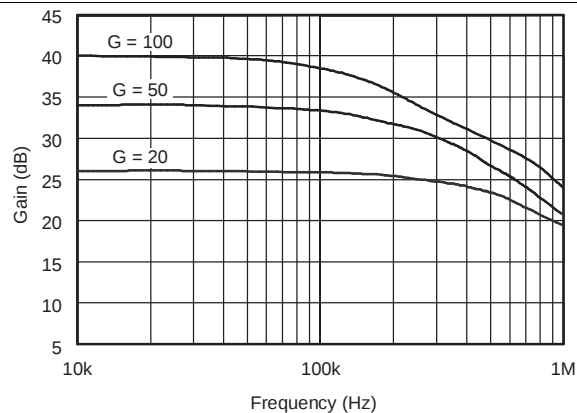


Figure 2. Gain vs Frequency

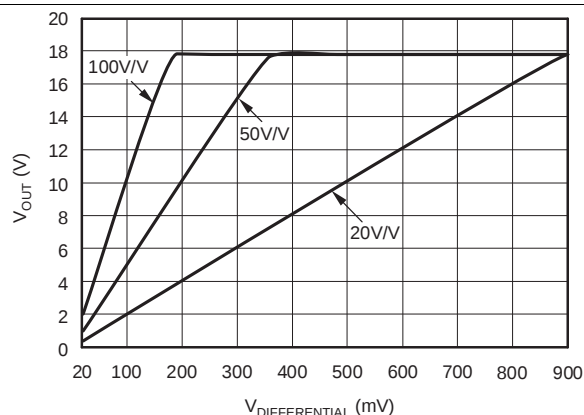


Figure 3. Gain Plot

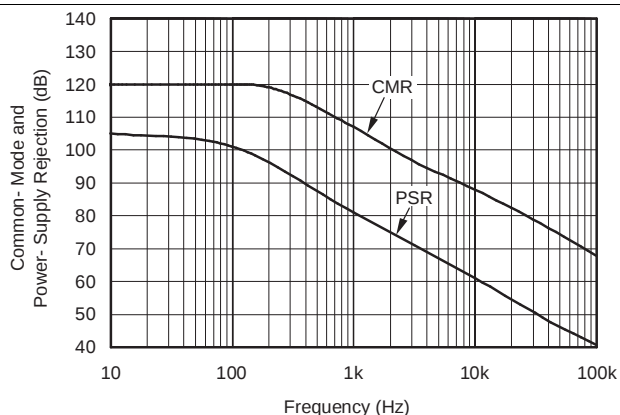


Figure 4. Common-Mode and Power-Supply Rejection vs Frequency

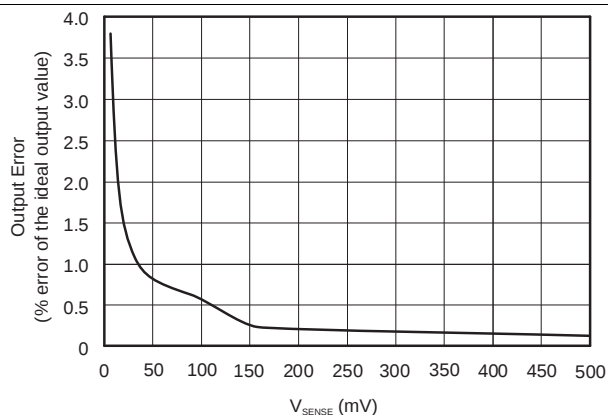


Figure 5. Output Error vs Vsense

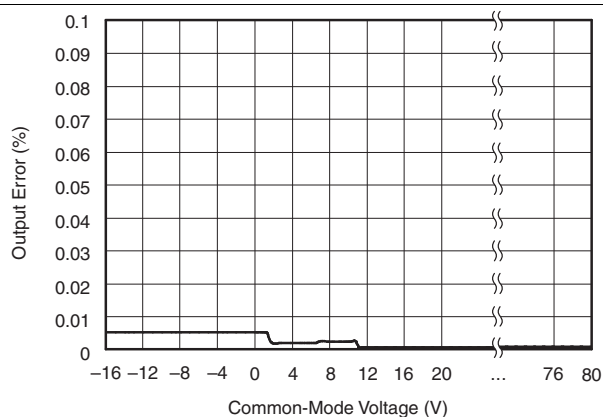


Figure 6. Output Error vs Common-Mode Voltage

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $V_S = 12\text{ V}$, $V_{IN+} = 12\text{ V}$, and $V_{SENSE} = 100\text{ mV}$ (unless otherwise noted)

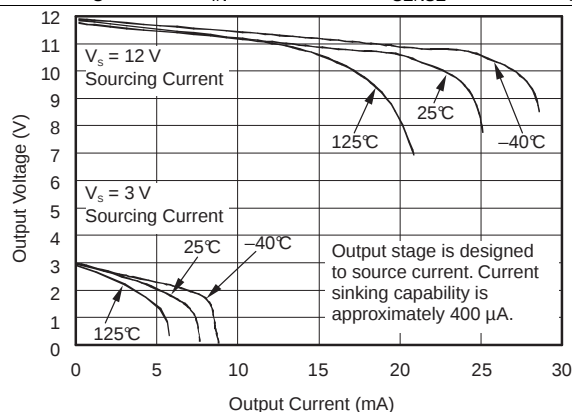


Figure 7. Positive Output Voltage Swing vs Output Current

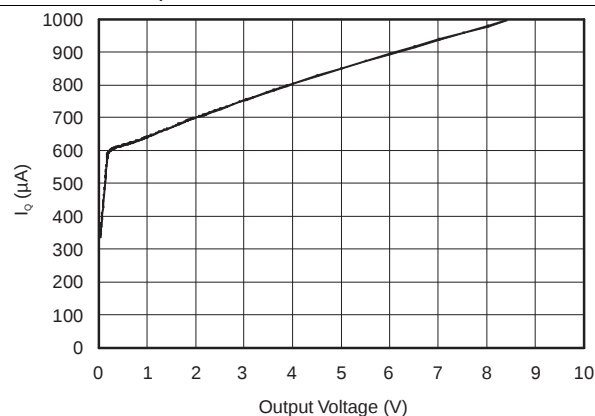


Figure 8. Quiescent Current vs Output Voltage

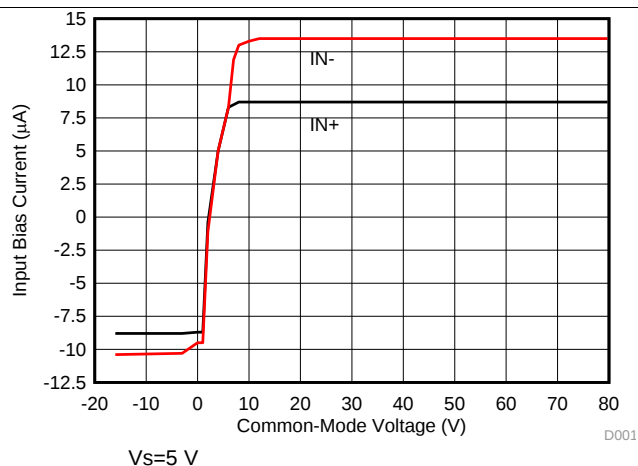


Figure 9. Input Bias Current vs Common Mode Voltage

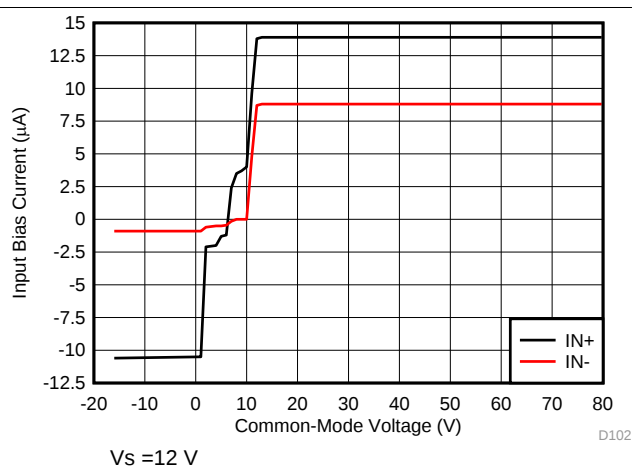


Figure 10. Input Bias Current vs Common Mode Voltage

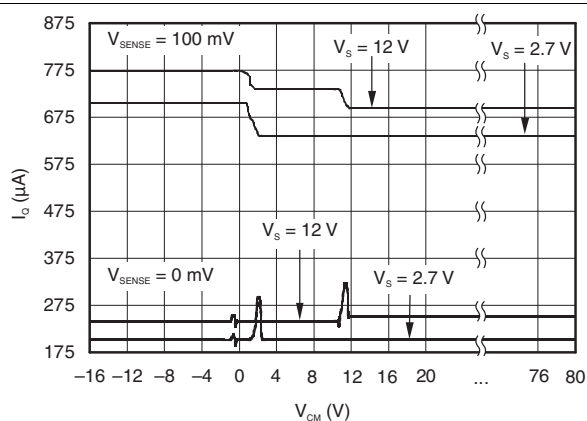


Figure 11. Quiescent Current vs Common Mode Voltage

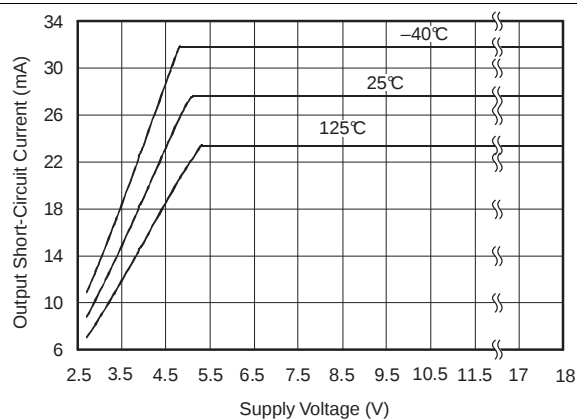


Figure 12. Output Short Circuit Current vs Supply Voltage

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $V_S = 12\text{ V}$, $V_{IN+} = 12\text{ V}$, and $V_{SENSE} = 100\text{ mV}$ (unless otherwise noted)

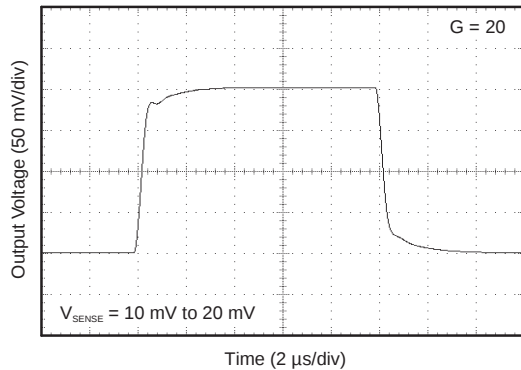


Figure 13. Step Response

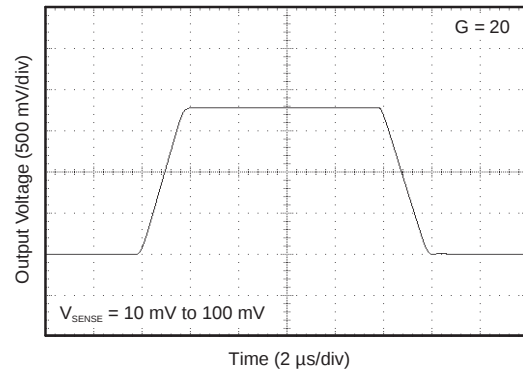


Figure 14. Step Response

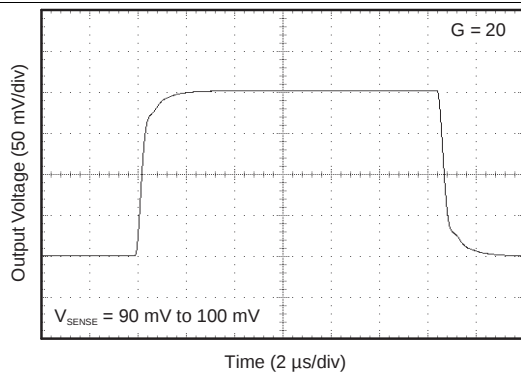


Figure 15. Step Response

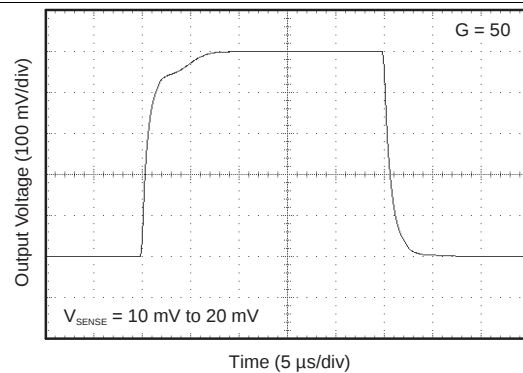


Figure 16. Step Response

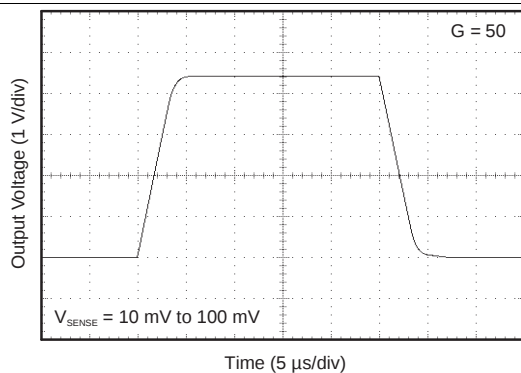


Figure 17. Step Response

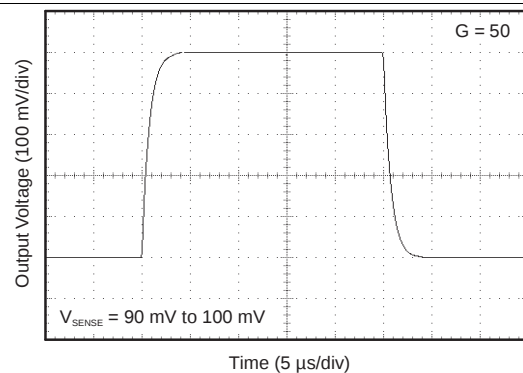


Figure 18. Step Response

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $V_S = 12\text{ V}$, $V_{IN+} = 12\text{ V}$, and $V_{SENSE} = 100\text{ mV}$ (unless otherwise noted)

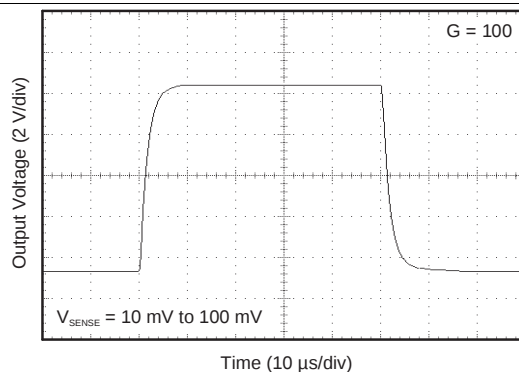


Figure 19. Step Response

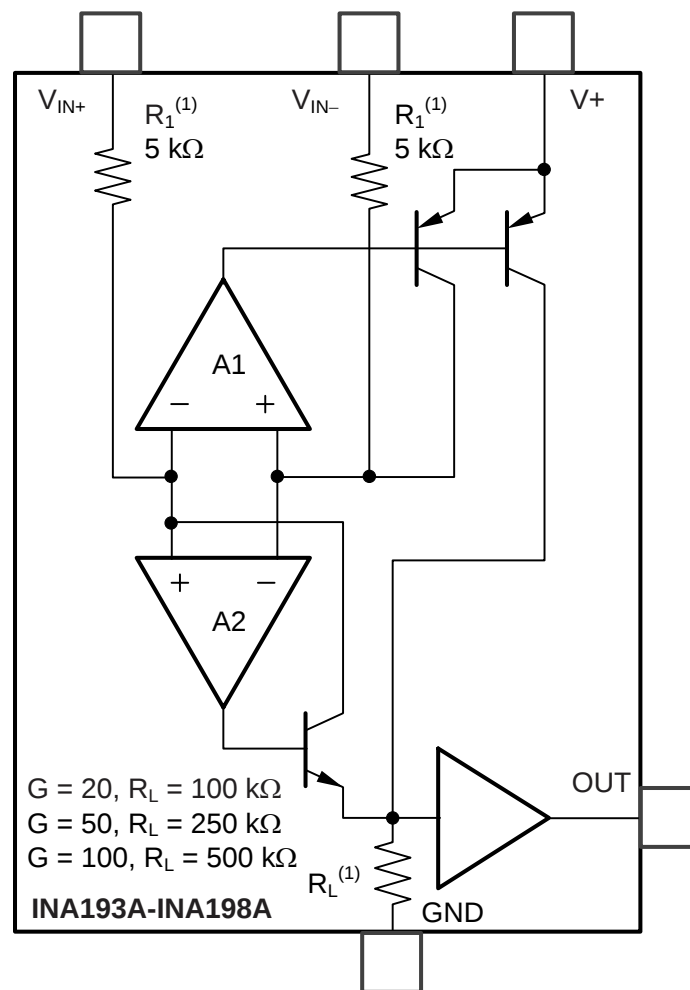
7 Detailed Description

7.1 Overview

The INA193A–INA198A family of current shunt monitors with voltage output can sense drops across shunts at common mode voltages from –16 V to 80 V, independent of the INA19x supply voltage. They are available with three output voltage scales: 20 V/V, 50 V/V, and 100 V/V. The 500-kHz bandwidth simplifies use in current control loops. The INA193A–INA195A devices provide identical functions but alternative pin configurations to the INA196A–INA198A, respectively.

The INA193A–INA198A devices operate from a single 2.7-V to 18-V supply, drawing a maximum of 900 μ A of supply current. They are specified over the extended operating temperature range (–40°C to 125°C), and are offered in a space-saving SOT-23 package.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Basic Connection

Figure 20 shows the basic connection of the INA19xA. The input pins, V_{IN+} and V_{IN-} , should be connected as closely as possible to the shunt resistor to minimize any resistance in series with the shunt resistance.

Power-supply bypass capacitors are required for stability. Applications with noisy or high-impedance power supplies may require additional decoupling capacitors to reject power-supply noise. Connect bypass capacitors close to the device pins.

Feature Description (continued)

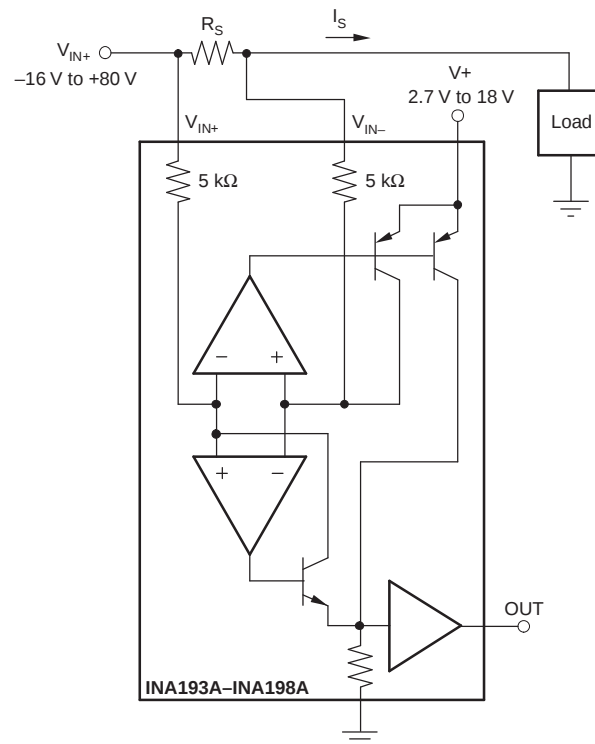


Figure 20. INA19xA Basic Connections

7.3.2 Selecting R_S

The value chosen for the shunt resistor, R_S , depends on the application and is a compromise between small-signal accuracy and maximum permissible voltage loss in the measurement line. High values of R_S provide better accuracy at lower currents by minimizing the effects of offset, while low values of R_S minimize voltage loss in the supply line. For most applications, best performance is attained with an R_S value that provides a full-scale shunt voltage range of 50 mV to 100 mV. Maximum input voltage for accurate measurements is 500 mV.

7.3.3 Inside the INA19xA

The INA19xA uses a new, unique, internal circuit topology that provides common mode range extending from –16 V to 80 V while operating from a single power supply. The common mode rejection in a classic instrumentation amplifier approach is limited by the requirement for accurate resistor matching. By converting the induced input voltage to a current, the INA19xA provides common mode rejection that is no longer a function of closely matched resistor values, providing the enhanced performance necessary for such a wide common mode range. A simplified diagram (see [Figure 20](#)) shows the basic circuit function. When the common mode voltage is positive, amplifier A2 is active.

The differential input voltage, $V_{IN+} - V_{IN-}$ applied across R_S , is converted to a current through a 5-kΩ resistor. This current is converted back to a voltage through R_L , and then amplified by the output buffer amplifier. When the common mode voltage is negative, amplifier A1 is active. The differential input voltage, $V_{IN+} - V_{IN-}$ applied across R_S , is converted to a current through a 5-kΩ resistor. This current is sourced from a precision current mirror whose output is directed into R_L , converting the signal back into a voltage and amplified by the output buffer amplifier. Patent-pending circuit architecture ensures smooth device operation, even during the transition period where both amplifiers A1 and A2 are active.

Feature Description (continued)

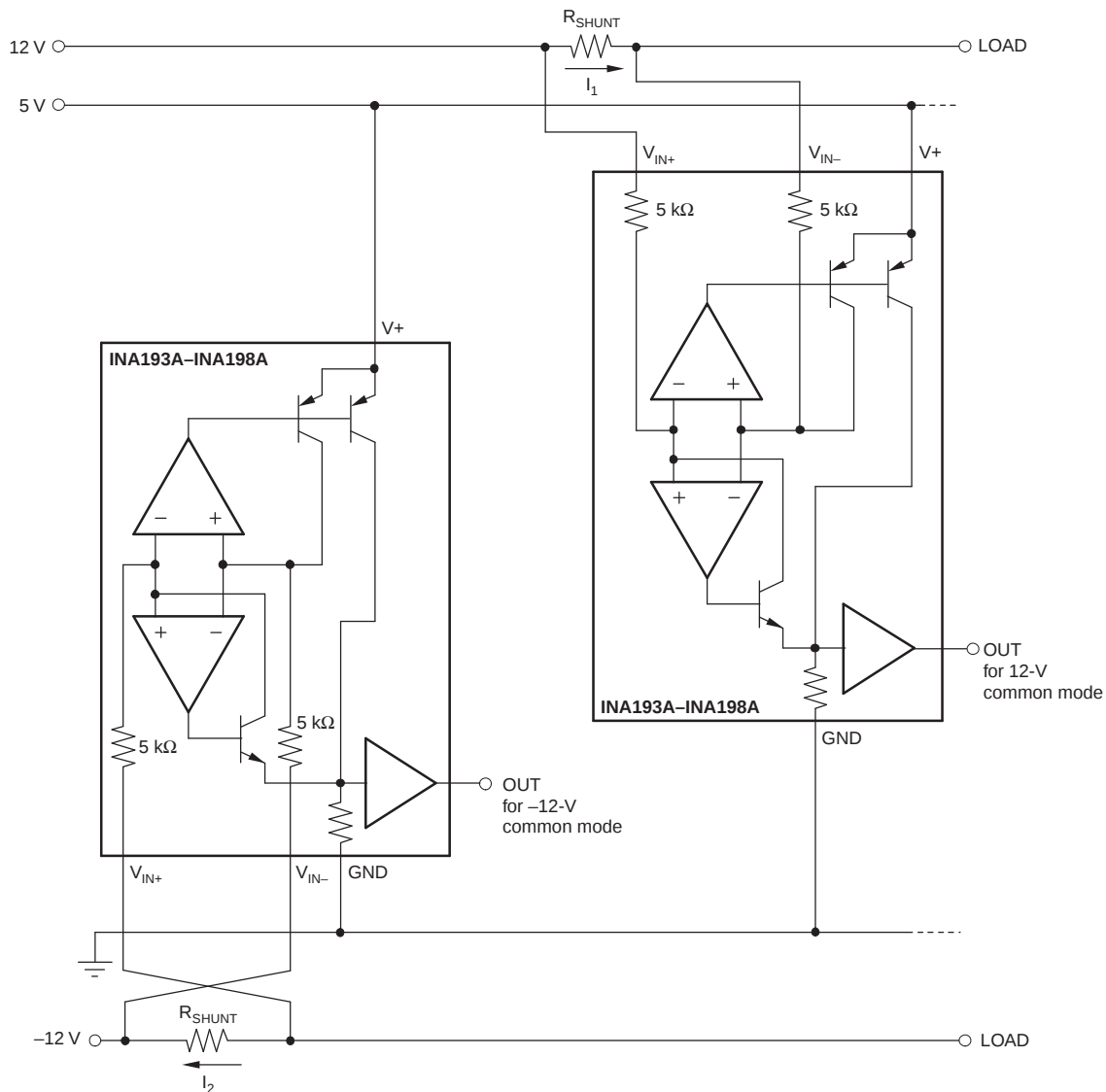


Figure 21. Monitor Bipolar Output Power-Supply Current

Feature Description (continued)

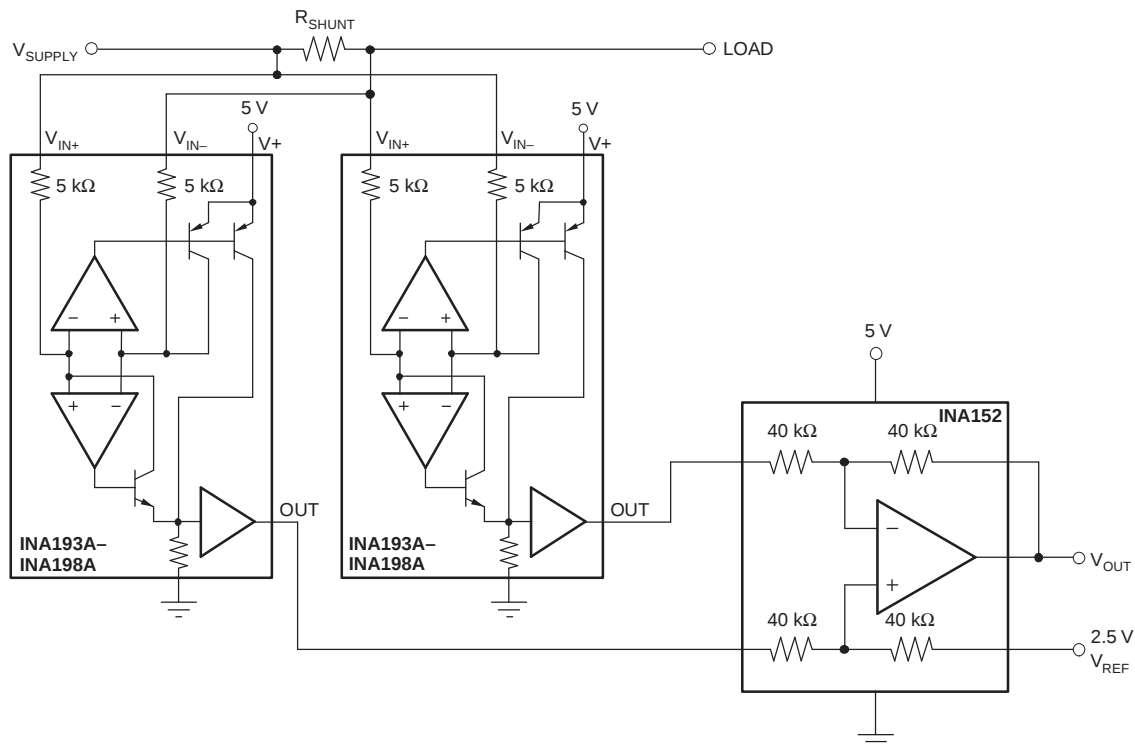


Figure 22. Bidirectional Current Monitoring

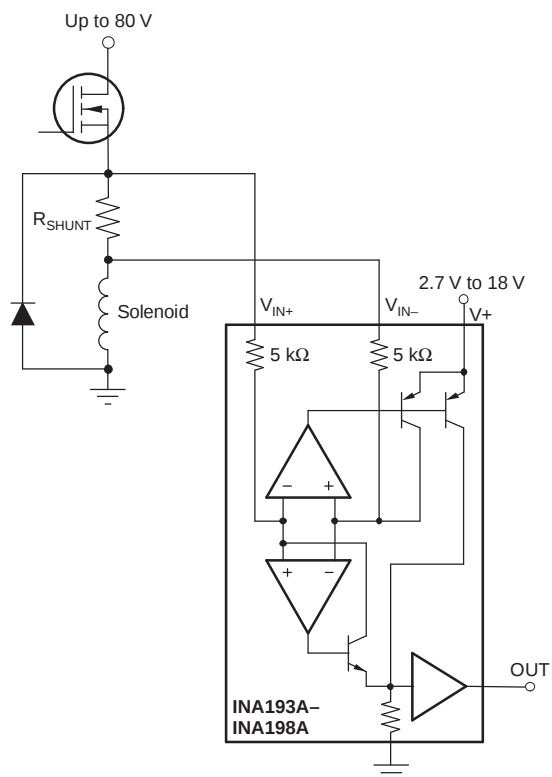
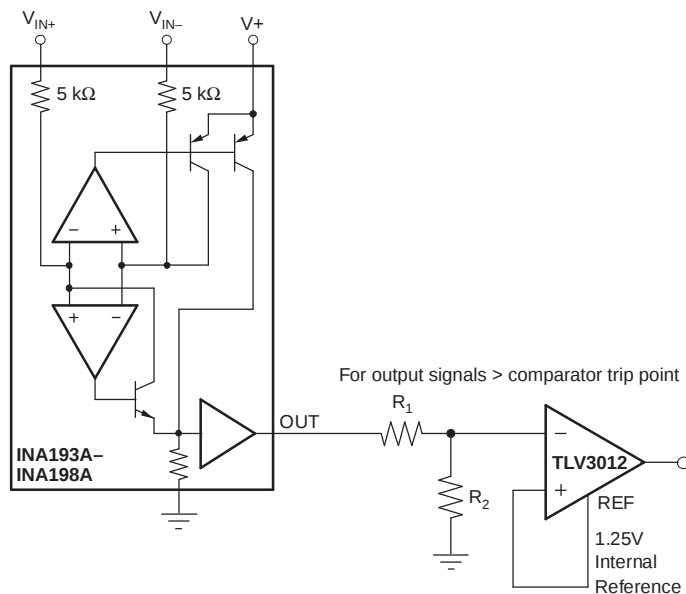
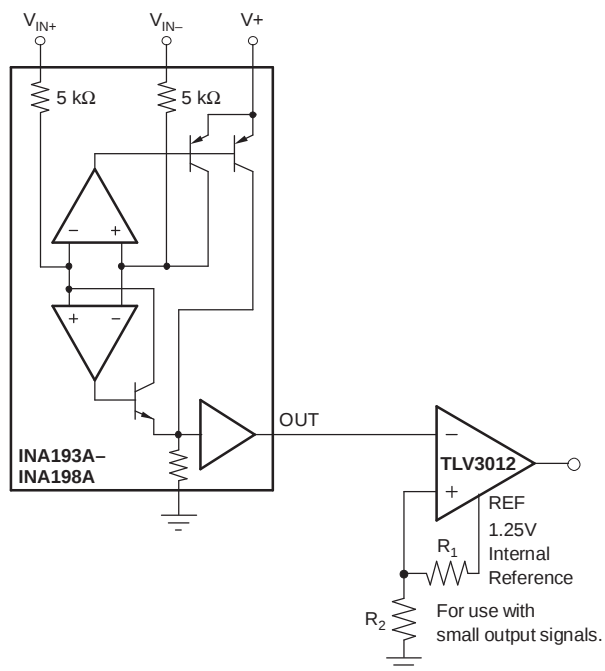


Figure 23. Inductive Current Monitor Including Flyback

Feature Description (continued)



(a) INA19xA Output Adjusted by Voltage Divider



(b) Comparator Reference Voltage Adjusted by Voltage Divider

Figure 24. INA19xA With Comparator

7.3.4 Power Supply

The input circuitry of the INA19xA can accurately measure beyond its power-supply voltage, V+. For example, the V+ power supply can be 5 V, whereas the load power-supply voltage is up to 80 V. The output voltage range of the OUT terminal, however, is limited by the voltages on the power-supply pin.

7.4 Device Functional Modes

7.4.1 Input Filtering

An obvious and straightforward location for filtering is at the output of the INA19xA series; however, this location negates the advantage of the low output impedance of the internal buffer. The only other option for filtering is at the input pins of the INA19xA, which is complicated by the internal 5-kΩ ± 30% input impedance (see Figure 25). Using the lowest possible resistor values minimizes both the initial shift in gain and effects of tolerance. The effect on initial gain is given by:

$$\text{Gain Error \%} = 100 - \left(100 \times \frac{5 \text{ k}\Omega}{5 \text{ k}\Omega + R_{\text{FILT}}} \right) \quad (1)$$

Total effect on gain error can be calculated by replacing the 5-kΩ term with 5 kΩ – 30% (or 3.5 kΩ) or 5 kΩ + 30% (or 6.5 kΩ). The tolerance extremes of R_{FILT} can also be inserted into the equation. If a pair of 100-Ω 1% resistors are used on the inputs, the initial gain error is 1.96%. Worst-case tolerance conditions always occur at the lower excursion of the internal 5-kΩ resistor (3.5 kΩ), and the higher excursion of R_{FILT} , 3% in this case.

The specified accuracy of the INA19xA must then be combined in addition to these tolerances. While this discussion treats accuracy worst-case conditions by combining the extremes of the resistor values, it is appropriate to use geometric mean or root sum square calculations to total the effects of accuracy variations.

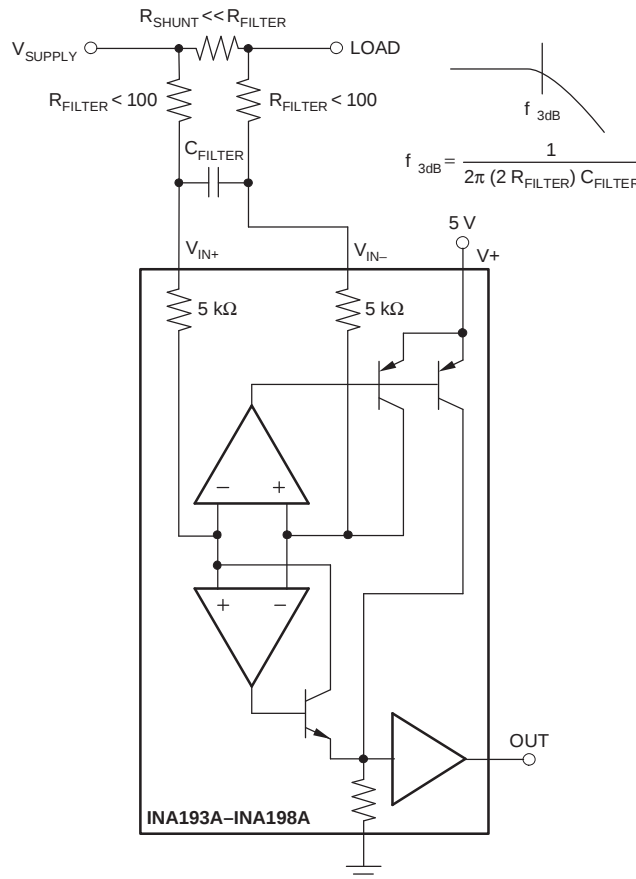


Figure 25. Input Filter (Gain Error = 1.5% to –2.2%)

7.4.2 Accuracy Variations as a Result Of V_{SENSE} and Common Mode Voltage

The accuracy of the INA19xA-Q1 current shunt monitors is a function of two main variables: V_{SENSE} ($V_{\text{IN+}} - V_{\text{IN-}}$) and common mode voltage, V_{CM} , relative to the supply voltage, V_{S} . V_{CM} is expressed as $(V_{\text{IN+}} + V_{\text{IN-}})/2$; however, in practice, V_{CM} is seen as the voltage at $V_{\text{IN+}}$ because the voltage drop across V_{SENSE} is usually small.

Device Functional Modes (continued)

This section addresses the accuracy of these specific operating regions:

- Normal Case 1: $V_{SENSE} \geq 20 \text{ mV}$, $V_{CM} \geq V_S$
 Normal Case 2: $V_{SENSE} \geq 20 \text{ mV}$, $V_{CM} < V_S$
 Low V_{SENSE} Case 1: $V_{SENSE} < 20 \text{ mV}$, $-16 \text{ V} \leq V_{CM} < 0$
 Low V_{SENSE} Case 2: $V_{SENSE} < 20 \text{ mV}$, $0 \text{ V} \leq V_{CM} \leq V_S$
 Low V_{SENSE} Case 3: $V_{SENSE} < 20 \text{ mV}$, $V_S < V_{CM} \leq 80 \text{ V}$

7.4.2.1 Normal Case 1: $V_{SENSE} \geq 20 \text{ mV}$, $V_{CM} \geq V_S$

This region of operation provides the highest accuracy. Here, the input offset voltage is characterized and measured using a two-step method. First, the gain is determined by (Equation 2).

$$G = \frac{V_{OUT1} - V_{OUT2}}{100 \text{ mV} - 20 \text{ mV}}$$

where

- V_{OUT1} = Output voltage with $V_{SENSE} = 100 \text{ mV}$
- V_{OUT2} = Output voltage with $V_{SENSE} = 20 \text{ mV}$

The offset voltage is then measured at $V_{SENSE} = 100 \text{ mV}$ and referred to the input (RTI) of the current shunt monitor, as shown in (Equation 3).

$$V_{OSRTI} (\text{Referred-To-Input}) = \left(\frac{V_{OUT1}}{G} \right) - 100 \text{ mV} \quad (3)$$

In the [Typical Characteristics](#), the *Output Error vs Common Mode Voltage* curve shows the highest accuracy for the this region of operation. In this plot, $V_S = 12 \text{ V}$; for $V_{CM} \geq 12 \text{ V}$, the output error is at its minimum. This case is also used to create the $V_{SENSE} \geq 20 \text{ mV}$ output specifications in the [Electrical Characteristics](#) table.

7.4.2.2 Normal Case 2: $V_{SENSE} \geq 20 \text{ mV}$, $V_{CM} < V_S$

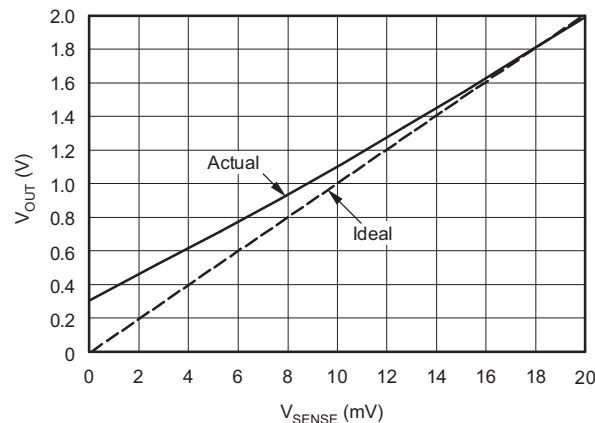
This region of operation has slightly less accuracy than Normal Case 1 as a result of the common mode operating area in which the part functions, as seen in [Figure 6](#). As noted, for this graph $V_S = 12 \text{ V}$; for $V_{CM} < 12 \text{ V}$, the Output Error increases as V_{CM} becomes less than 12 V , with a typical maximum error of 0.005% at the most negative $V_{CM} = -16 \text{ V}$.

7.4.2.3 Low V_{SENSE} Case 1: $V_{SENSE} < 20 \text{ mV}$, $-16 \text{ V} \leq V_{CM} < 0$; and Low V_{SENSE} Case 3: $V_{SENSE} < 20 \text{ mV}$, $V_S < V_{CM} \leq 80 \text{ V}$

Although the INA19xA-Q1 family of devices are not designed for accurate operation in either of these regions, some applications are exposed to these conditions; for example, when monitoring power supplies that are switched on and off while V_S is still applied to the INA19xA-Q1. It is important to know what the behavior of the devices will be in these regions.

As V_{SENSE} approaches 0 mV , in these V_{CM} regions, the device output accuracy degrades. A larger-than-normal offset can appear at the current shunt monitor output with a typical maximum value of $V_{OUT} = 300 \text{ mV}$ for $V_{SENSE} = 0 \text{ mV}$. As V_{SENSE} approaches 20 mV , V_{OUT} returns to the expected output value with accuracy as specified in [Electrical Characteristics](#). [Figure 26](#) illustrates this effect using the INA195A and INA198A (Gain = 100).

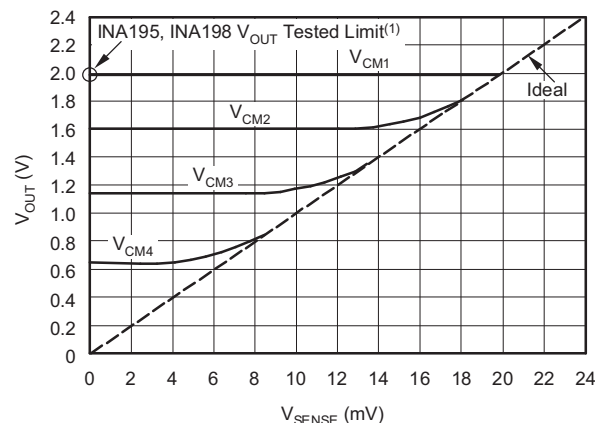
Device Functional Modes (continued)



**Figure 26. Example for Low V_{SENSE} Cases 1 and 3
(INA195A-Q1, INA198A-Q1: Gain = 100)**

7.4.2.4 Low V_{SENSE} Case 2: $V_{SENSE} < 20$ mV, 0 V $\leq V_{CM} \leq V_S$

This region of operation is the least accurate for the INA19xA-Q1 family. To achieve the wide input common mode voltage range, these devices use two operational amplifier front ends in parallel. One operational amplifier front end operates in the positive input common mode voltage range, and the other in the negative input region. For this case, neither of these two internal amplifiers dominates and overall loop gain is very low. Within this region, V_{OUT} approaches voltages close to linear operation levels for Normal Case 2. This deviation from linear operation becomes greatest the closer V_{SENSE} approaches 0 V. Within this region, as V_{SENSE} approaches 20 mV, device operation is closer to that described by Normal Case 2. Figure 27 illustrates this behavior for the INA195A. The V_{OUT} maximum peak for this case is tested by maintaining a constant V_S , setting $V_{SENSE} = 0$ mV and sweeping V_{CM} from 0 V to V_S . The exact V_{CM} at which V_{OUT} peaks during this test varies from part to part, but the V_{OUT} maximum peak is tested to be less than the specified V_{OUT} tested limit.



(1) INA193, INA196 V_{OUT} Tested Limit = 0.4 V

INA194, INA197 V_{OUT} Tested Limit = 1 V

NOTE: V_{OUT} tested limit at $V_{SENSE} = 0$ mV, $0 \leq V_{CM1} \leq V_S$.

V_{CM2} , V_{CM3} , and V_{CM4} illustrate the variance from part to part of the V_{CM} that can cause maximum V_{OUT} with $V_{SENSE} < 20$ mV.

**Figure 27. Example for Low V_{SENSE} Case 2
(INA195A, INA198A: Gain = 100)**

Device Functional Modes (continued)

7.4.3 Shutdown

Because the INA19xA-Q1 consume a quiescent current less than 1 mA, they can be powered by either the output of logic gates or by transistor switches to supply power. Use a totem pole output buffer or gate that can provide sufficient drive along with 0.1 μ F bypass capacitor, preferably ceramic with good high frequency characteristics. This gate should have a supply voltage of 3 V or greater because the INA19xA-Q1 requires a minimum supply greater than 2.7 V. In addition to eliminating quiescent current, this gate also turns off the 10 μ A bias current present at each of the inputs. An example shutdown circuit is shown in Figure 28.

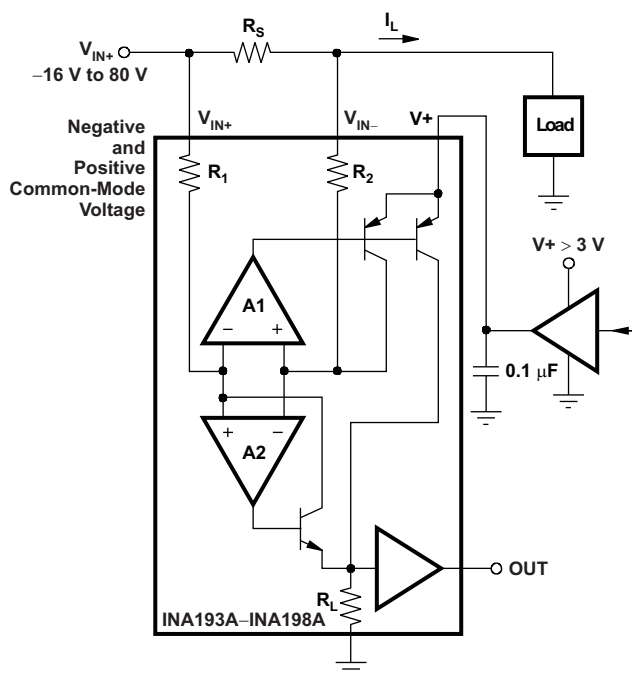


Figure 28. INA19xA-Q1 Example Shutdown Circuit

7.4.4 Transient Protection

The -16-V to 80-V common mode range of the INA19xA is ideal for withstanding automotive fault conditions ranging from 12-V battery reversal up to 80-V transients, because no additional protective components are needed up to those levels. In the event that the INA19xA is exposed to transients on the inputs in excess of its ratings, then external transient absorption with semiconductor transient absorbers (zeners or Transzorbs) are necessary. TI does not recommend using MOVs or VDRs except when they are used in addition to a semiconductor transient absorber. Select the transient absorber such that it never allows the INA19xA to be exposed to transients greater than 80 V (that is, allow for transient absorber tolerance, as well as additional voltage due to transient absorber dynamic impedance). Despite the use of internal zener-type ESD protection, the INA19xA does not lend itself to using external resistors in series with the inputs because the internal gain resistors can vary up to $\pm 30\%$. (If gain accuracy is not important, then resistors can be added in series with the INA19xA inputs with two equal resistors on each input.)

7.4.5 Output Voltage Range

The output of the INA19xA is accurate within the output voltage swing range set by the power supply pin, V+. This is best illustrated when using the INA195A or INA198A (which are both versions using a gain of 100), where a 100-mV full-scale input from the shunt resistor requires an output voltage swing of 10 V, and a power-supply voltage sufficient to achieve 10 V on the output.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The INA193A-INA198A devices measure the voltage developed across a current-sensing resistor when current passes through it. The ability to have shunt common mode voltages from -16 V to 80 V drive and control the output signal with V_S offers multiple configurations, as discussed throughout this section.

8.2 Typical Application

The device is a unidirectional, current-sense amplifier capable of measuring currents through a resistive shunt with shunt common mode voltages from -16 V to 80 V . Two devices can be configured for bidirectional monitoring and is common in applications that include charging and discharging operations where the current flow-through resistor can change directions.

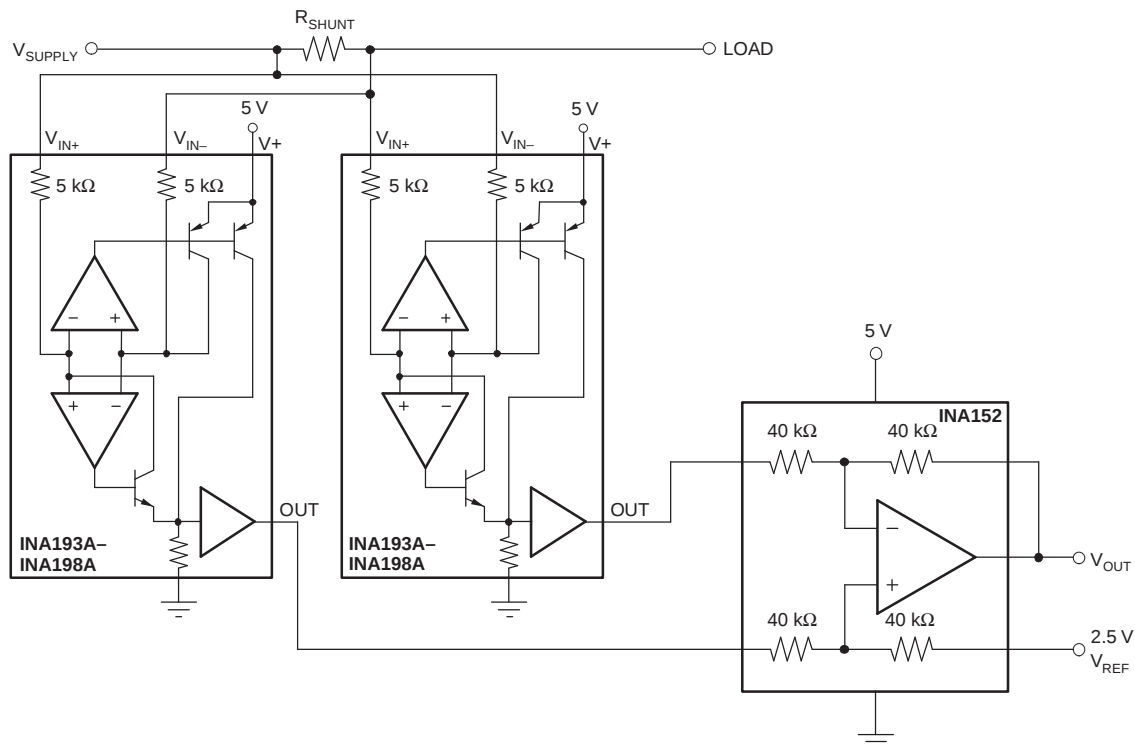


Figure 29. Bidirectional Current Monitoring

8.2.1 Design Requirements

V_{supply} is set to 12 V , V_{ref} at 2.5 V and a $10\text{-m}\Omega$ shunt. The accuracy of the current will typically be less than 0.5% for current greater than $\pm 2\text{ A}$. For current lower than $\pm 2\text{ A}$, the accuracy will vary; use the [Accuracy Variations as a Result Of \$V_{SENSE}\$ and Common Mode Voltage](#) section for accuracy considerations.

Typical Application (continued)

8.2.2 Detailed Design Procedure

The ability to measure this current flowing in both directions is enabled by adding a unity gain amplifier with a V_{REF} , as shown in Figure 29. The output then responds by increasing above V_{REF} for positive differential signals (relative to the IN – pin) and responds by decreasing below V_{REF} for negative differential signals. This reference voltage applied to the REF pin can be set anywhere from 0 V to $V+$. For bidirectional applications, V_{REF} is typically set at mid-scale for equal signal range in both current directions. In some cases, however, V_{REF} is set at a voltage other than mid-scale when the bidirectional current and corresponding output signal are not required to be symmetrical.

8.2.3 Application Curve

An example output response of a bidirectional configuration is shown in Figure 30. With the REF pin connected to a reference voltage, 2.5 V in this case, the output voltage is biased upwards by this reference level. The output rises above the reference voltage for positive differential input signals and falls below the reference voltage for negative differential input signals.

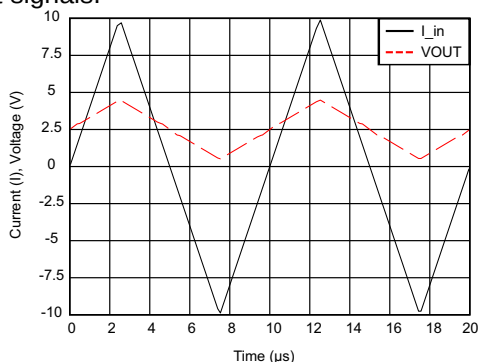


Figure 30. Output Voltage vs Shunt Input Current

9 Power Supply Recommendations

The input circuitry of the INA193A-INA198A devices can accurately measure beyond its power-supply voltage, $V+$. For example, the $V+$ power supply can be 5 V, whereas the load power-supply voltage is up to 80 V. The output voltage range of the OUT terminal, however, is limited by the voltages on the power-supply pin.

10 Layout

10.1 Layout Guidelines

10.1.1 RFI/EMI

TI always recommends adhering to good layout practices. Keep traces short and, when possible, use a printed-circuit-board (PCB) ground plane with surface-mount components placed as close to the device pins as possible. Small ceramic capacitors placed directly across amplifier inputs can reduce RFI/EMI sensitivity. PCB layout should locate the amplifier as far away as possible from RFI sources. Sources can include other components in the same system as the amplifier itself, such as inductors (particularly switched inductors handling a lot of current and at high frequencies). RFI can generally be identified as a variation in offset voltage or dc signal levels with changes in the interfering RF signal. If the amplifier cannot be located away from sources of radiation, shielding may be needed. Twisting wire input leads makes them more resistant to RF fields. The difference in input pin location of the INA193A–INA195A versus the INA196A–INA198A may provide different EMI performance.

10.2 Layout Example

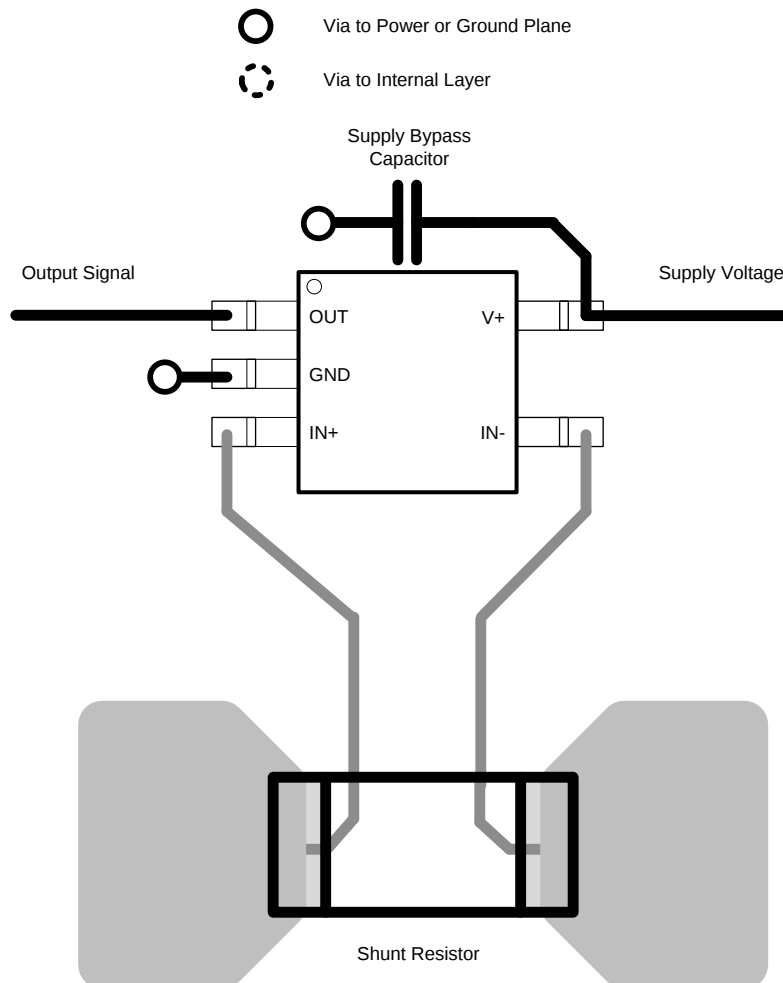


Figure 31. Recommended Layout

11 器件和文档支持

11.1 相关链接

下面的表格中列出了快速访问链接。范围包括技术文档、支持和社区资源、工具和软件，以及样片或购买的快速访问。

表 1. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
INA193A-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA194A-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA195A-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA196A-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA197A-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA198A-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

11.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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11.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

11.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA193AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BOG	Samples
INA194AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BOH	Samples
INA195AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BOI	Samples
INA196AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BOJ	Samples
INA197AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BOK	Samples
INA198AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BOL	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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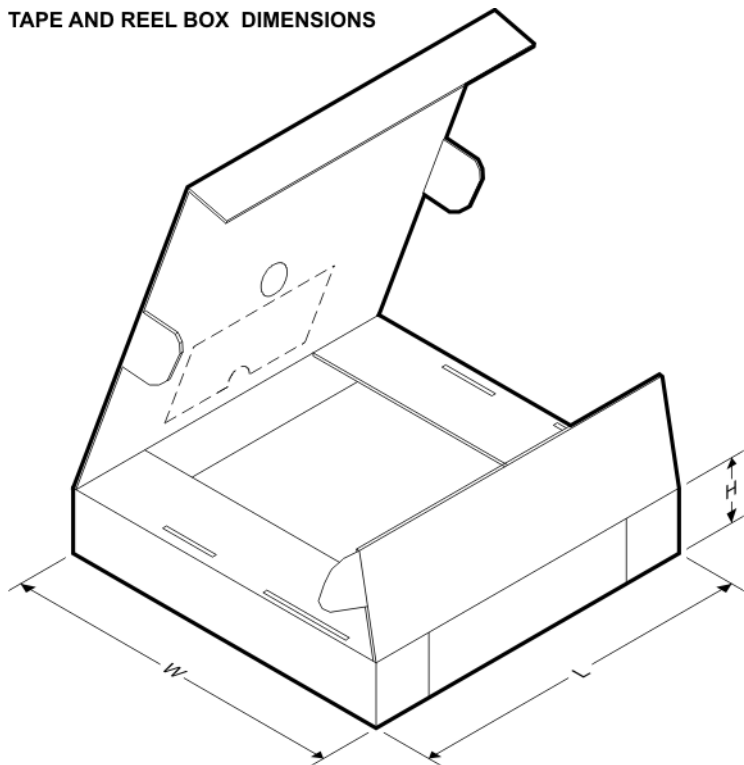
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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA193AQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
INA194AQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
INA195AQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
INA196AQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
INA197AQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
INA198AQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA193AQDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0
INA194AQDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0
INA195AQDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0
INA196AQDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0
INA197AQDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0
INA198AQDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0

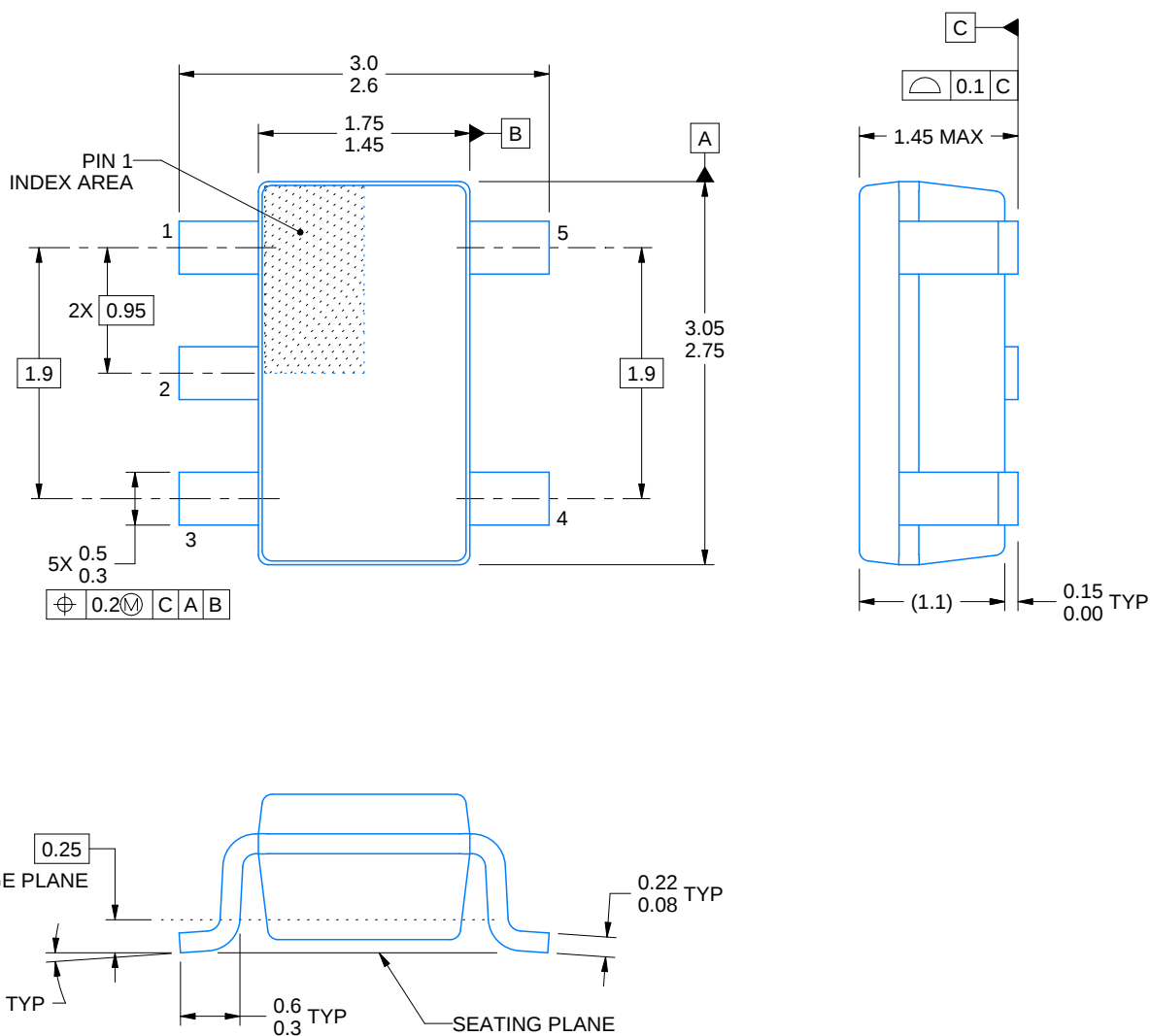


DBV0005A

PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214839/D 11/2018

NOTES:

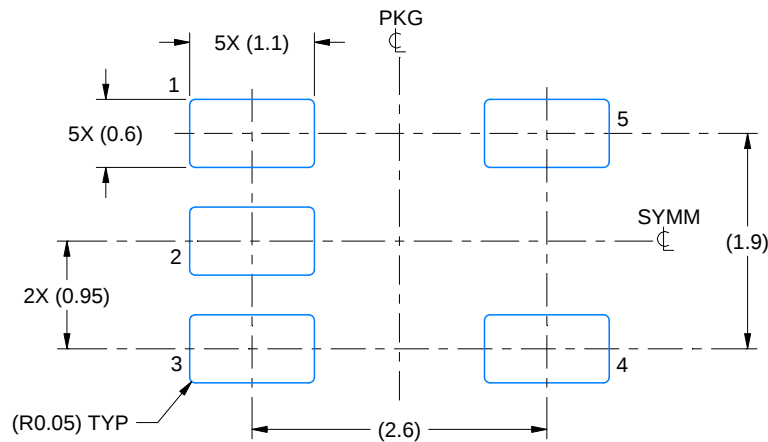
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

EXAMPLE BOARD LAYOUT

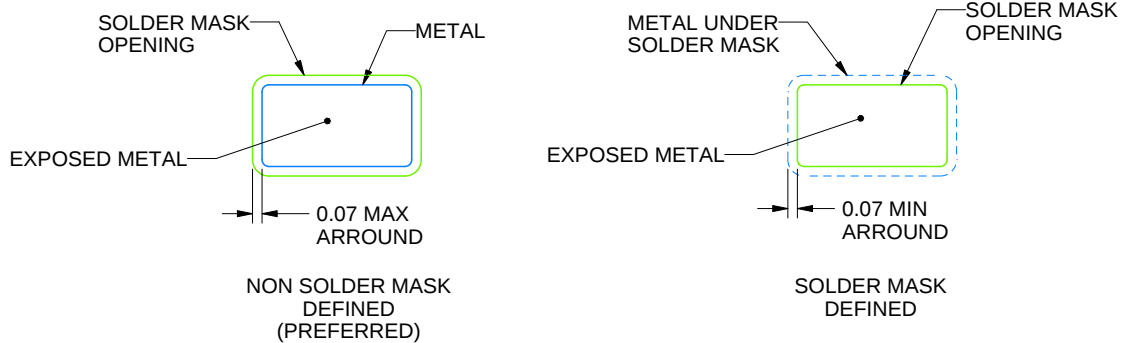
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/D 11/2018

NOTES: (continued)

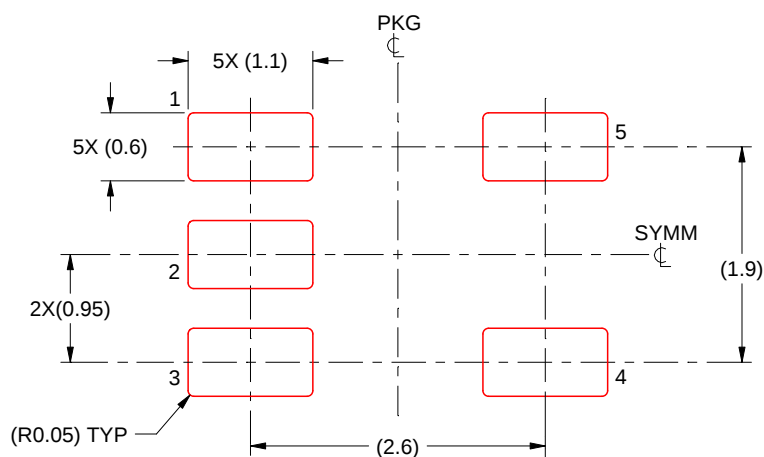
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/D 11/2018

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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